

Figure 1. Output Characteristics

Figure 2. Transfer Characteristics

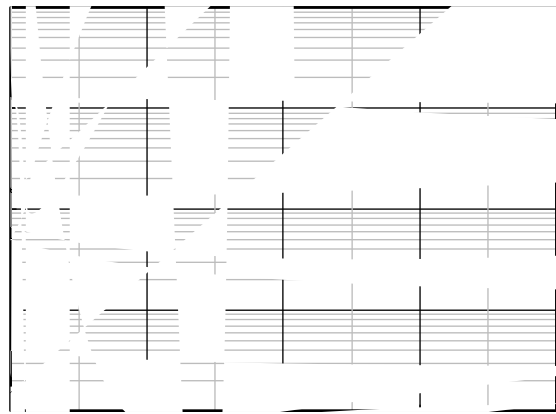


Figure 3. Capacitance Characteristics

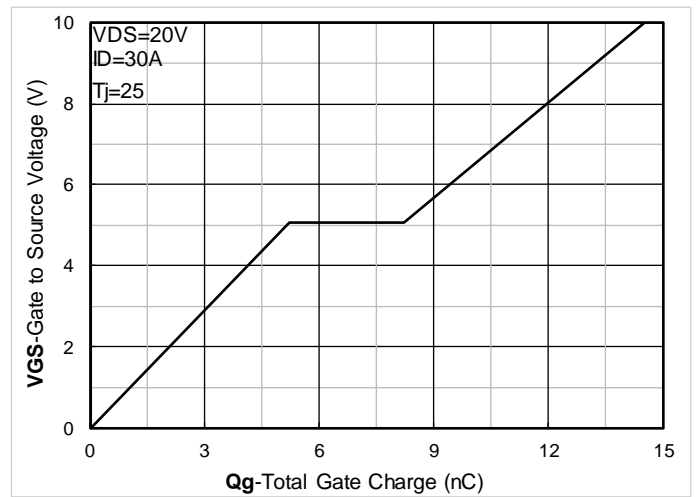


Figure 4. Gate Charge

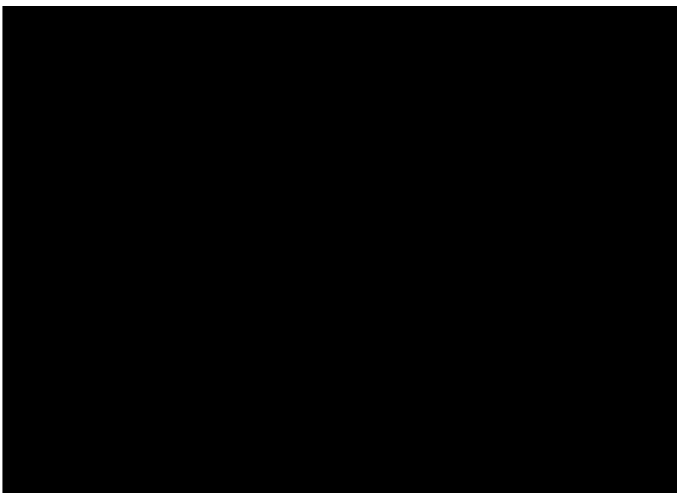


Figure 5. On-Resistance vs Gate to Source Voltage

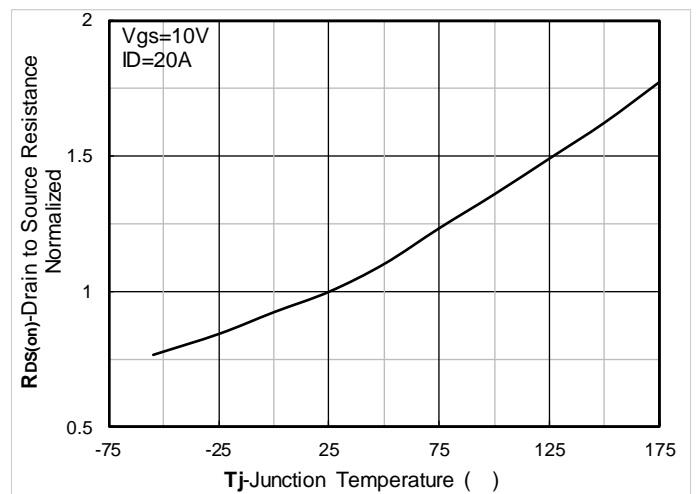


Figure 6. Normalized On-Resistance



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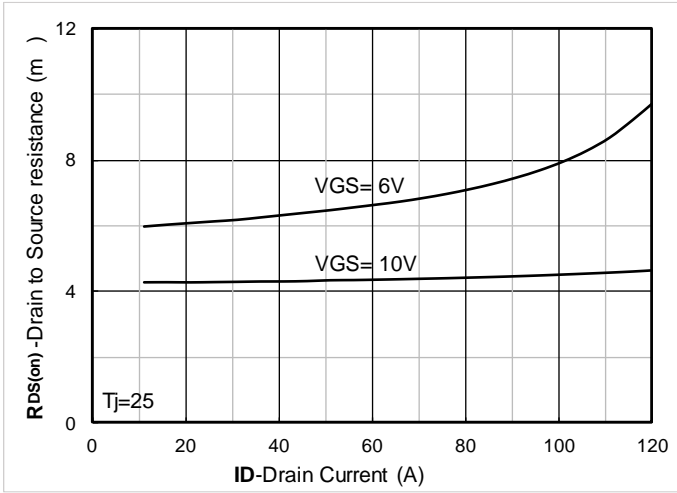


Figure 7. RDS(on) VS Drain Current

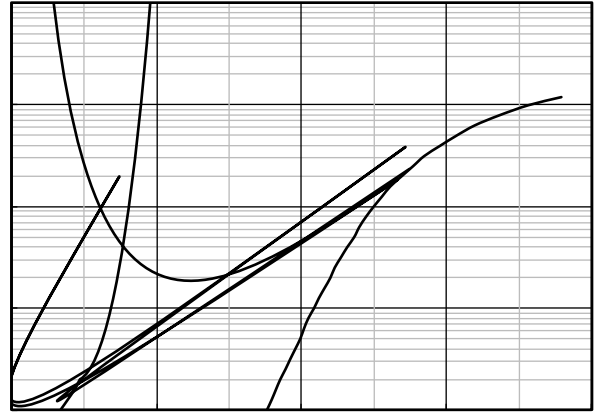


Figure 8. Forward characteristics of reverse diode

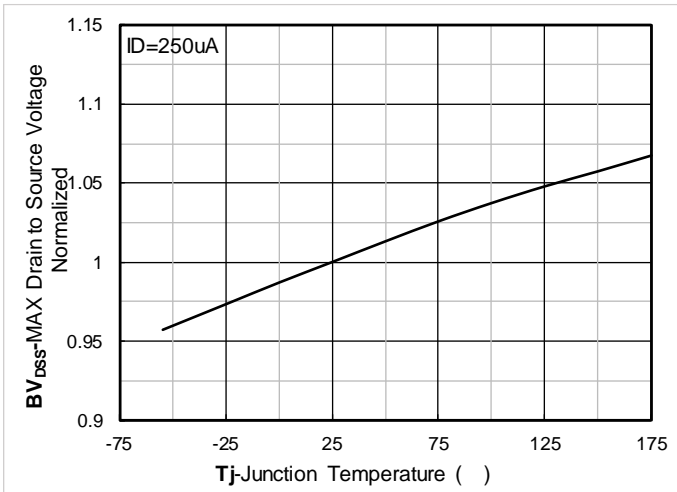


Figure 9. Normalized breakdown voltage

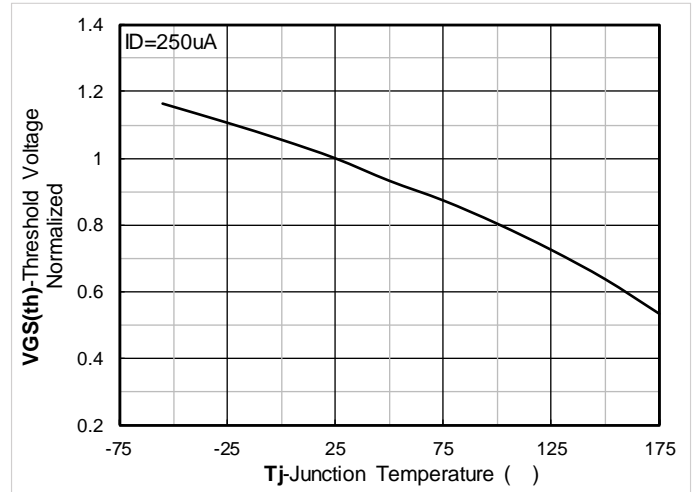


Figure 10. Normalized Threshold voltage

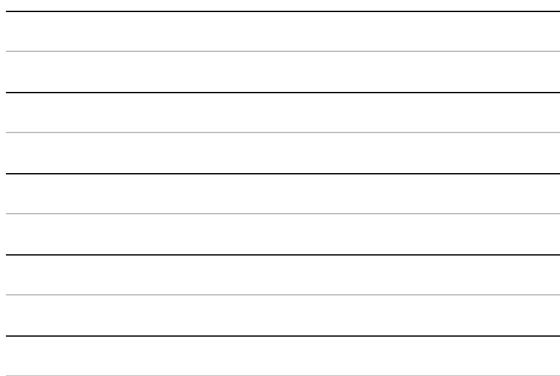


Figure 11. Current dissipation

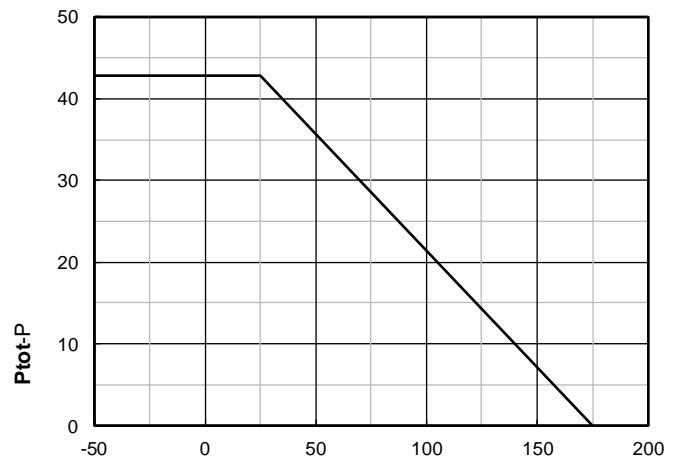


Figure 12. Power dissipation

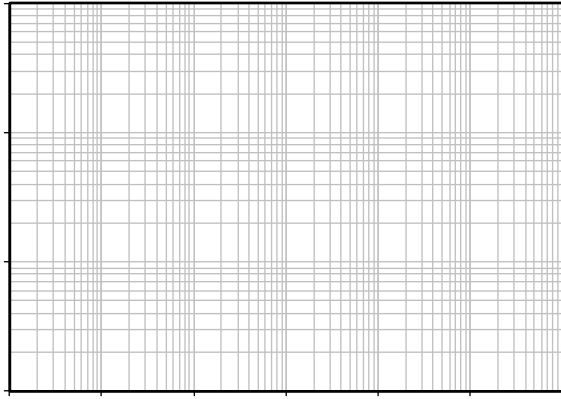


Figure 13. Maximum Transient Thermal Impedance

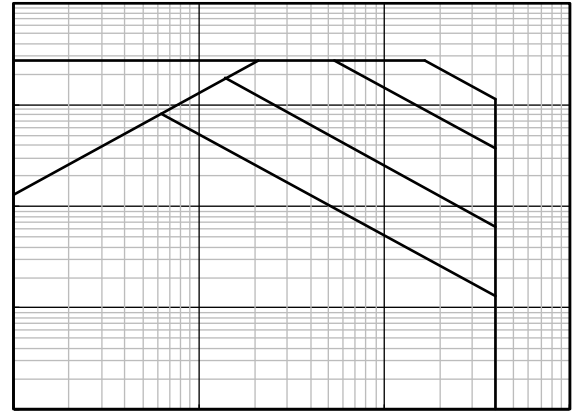


Figure 14. Safe Operation Area

## Test Circuits & Waveforms



Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

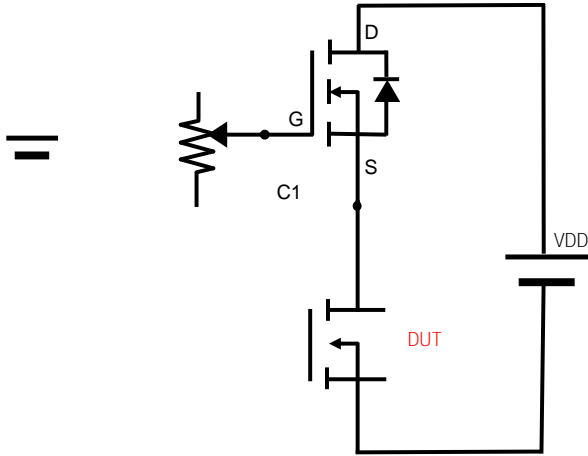


Figure B. Gate Charge Test Circuit & Waveform

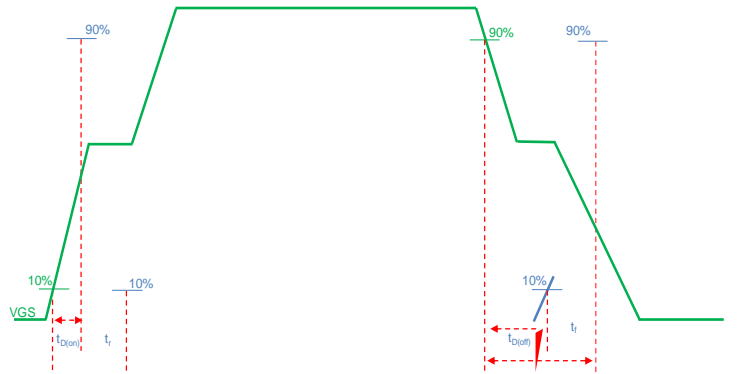
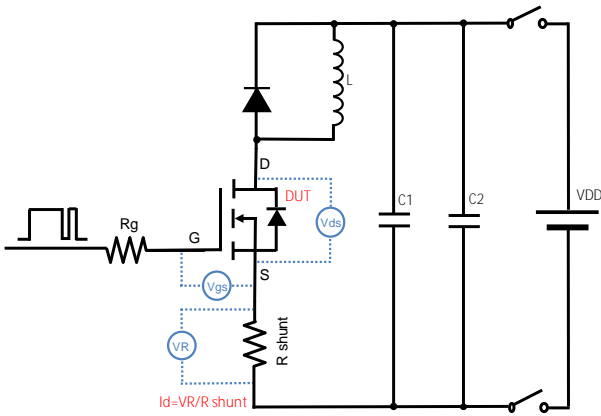


Figure C. Resistive Switching Test Circuit & Waveform

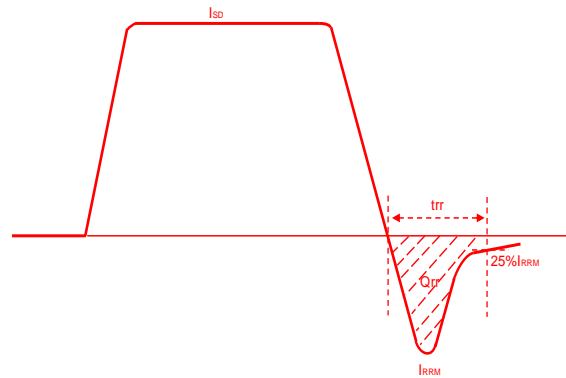
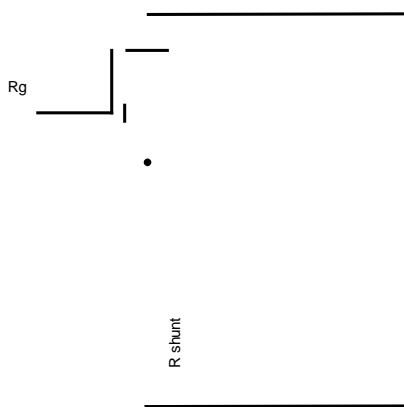
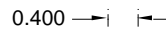
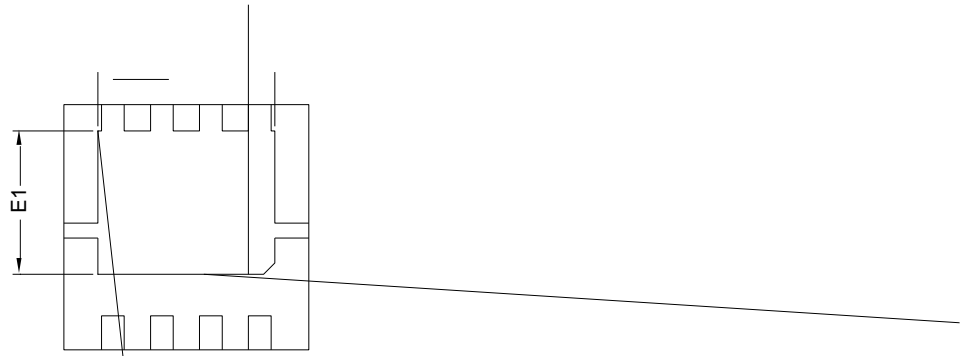


Figure D. Diode Recovery Test Circuit & Waveform



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## DFN3333-8L-A-0.8MM Package information



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.10$ mm.
  3. The pad layout is for reference purposes only.

Suggested Solder Pad Layout  
Top View



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## Disclaimer

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